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(71) Applicants: **BOE TECHNOLOGY GROUP CO., LTD.** [CN/CN]; No.10 Jiuxianqiao Rd., Chaoyang District, Beijing 100015 (CN). **CHENGDU BOE OPTOELECTRONICS TECHNOLOGY CO., LTD.** [CN/CN]; No.1188 Hezuo Rd., (West Zone), Hi-tech Development Zone, Chengdu, Sichuan 611731 (CN).

(72) Inventors: **ZHANG, Tiaomei**; No.9 Dize Rd., BDA, Daxing District, Beijing 100176 (CN). **GAO, Wenhui**; No.9 Dize Rd., BDA, Daxing District, Beijing 100176 (CN). **JIANG, Zhiliang**; No.9 Dize Rd., BDA, Daxing District, Beijing 100176 (CN). **WU, Jianpeng**; No.9 Dize Rd., BDA, Daxing District, Beijing 100176 (CN). **HU, Ming**; No.9 Dize Rd., BDA, Daxing District, Beijing 100176 (CN).

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(54) Title: ARRAY SUBSTRATE AND DISPLAY APPARATUS

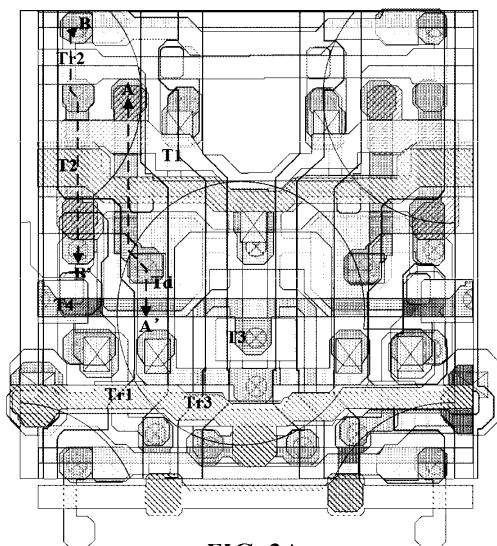


FIG. 3A

(57) Abstract: An array substrate. The array substrate includes a plurality of pixel driving circuits; wherein a respective pixel driving circuit (PDC) of the plurality of pixel driving circuits comprises a driving transistor (Td), a first light emitting control transistor (T3), and a third reset transistor (Tr3); active layers (ACTd, ACT3, ACTr3) of the driving transistor (Td), the first light emitting control transistor (T3), and the third reset transistor (Tr3) are in a first semiconductor material layer (SML1); a first electrode (Sd) of the driving transistor (Td), a second electrode (D3) of the first light emitting control transistor (T3), and a second electrode (Dr3) of the third reset transistor (Tr3) are in the first semiconductor material layer (SML1); the first electrode (Sd) of the driving transistor (Td), the second electrode (D3) of the first light emitting control transistor (T3), and the second electrode (Dr3) of the third reset transistor (Tr3) are parts of a unitary structure; and the first electrode (Sd) of the driving transistor (Td), the second electrode (D3) of the first light emitting control transistor (T3), and the second electrode (Dr3) of the third reset transistor (Tr3) are connected to each other by one or more portions of the first semiconductor material layer (SML1).

WO 2025/065209 A1